

10RIA120M

1

Features

- Hermetic glass -metal seal
- tested according to IEC standards

10A

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC switch and thermal control
- Synchronous motor excitation

Major Ratings and Characteristics

Parameters	10RIA120M	Units
$I_{T(AV)}$	10	A
@ T_c	85	°C
$I_{T(RMS)}$	16	A
I_{TSM}	310	A
@ 50Hz	322	A
$I^2 t$	523	$A^2 s$
@ 60Hz	477	$A^2 s$
V_{DRM} / V_{RRM}	400 to 1600	V
T_q typical	200	μs
T_J range	- 40 to 125	°C

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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} / V_{DRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak rev. voltage V	I_{RRM} / I_{DRM} max. @ $T_J = T_{J \text{ max.}}$ mA
10RIA120M	04	400	500	10
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

On-state Conduction

Parameter	10RIA 120M	Units	Conditions								
$I_{T(AV)}$ @ Case temperature	10	A	180° conduction, half sine wave								
	85	°C									
$I_{T(RMS)}$	16	A									
I_{TSM} , Maximum peak, one-cycle non-repetitive surge current	310	A	$t = 10\text{ms}$	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_{J \text{ max.}}$						
	322		$t = 8.3\text{ms}$								
	260		$t = 10\text{ms}$	100% V_{RRM} reapplied							
	272		$t = 8.3\text{ms}$								
$I^2 t$ Maximum $I^2 t$ for fusing	522	$\text{A}^2 \text{s}$	$t = 10\text{ms}$	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_{J \text{ max.}}$						
	477		$t = 8.3\text{ms}$								
	368		$t = 10\text{ms}$	100% V_{RRM} reapplied							
	336		$t = 8.3\text{ms}$								
$I^2 \sqrt{t}$	5227	$\text{A}^2 \sqrt{\text{s}}$	$t = 0.1 \text{ to } 10\text{ms}$, no voltage reapplied, $T_J = T_{J \text{ max.}}$								
V_{TM}	1.64	V	$I_{pk} = 63 \text{ A}$, $T_J = 25^\circ\text{C}$								
I_H	130	mA	$T_J = 25^\circ\text{C}$, anode supply 6V resistive load								
I_L	200										

Switching

Parameter	10RIA 120M	Units	Conditions	
di/dt	Max. rate of rise of turned-on current	$\text{A}/\mu\text{s}$	Gate pulse 20V, 15Ω , $t_r \leq 1\mu\text{s}$, $T_J = T_{J \text{ max.}}$	
t_d	ical delay time	μs	Gate current 1A, $di/dt = 1\text{A}/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ\text{C}$	
T_{fT}	pical turn-off time	μs	$I_{TM} = IT_{(AV)}$, $T_J = T_{J \text{ max.}}$, $t_p > 200\mu\text{s}$, $V_R = 100\text{V}$, $di/dt = -10\text{A}/\mu\text{s}$, $dv/dt = 20\text{V}/\mu\text{s}$,	

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Blocking

Parameter	10RIA120M	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	100	V/μs	T _J = T _J max linear to 100% rated V _{DRM}

Triggering

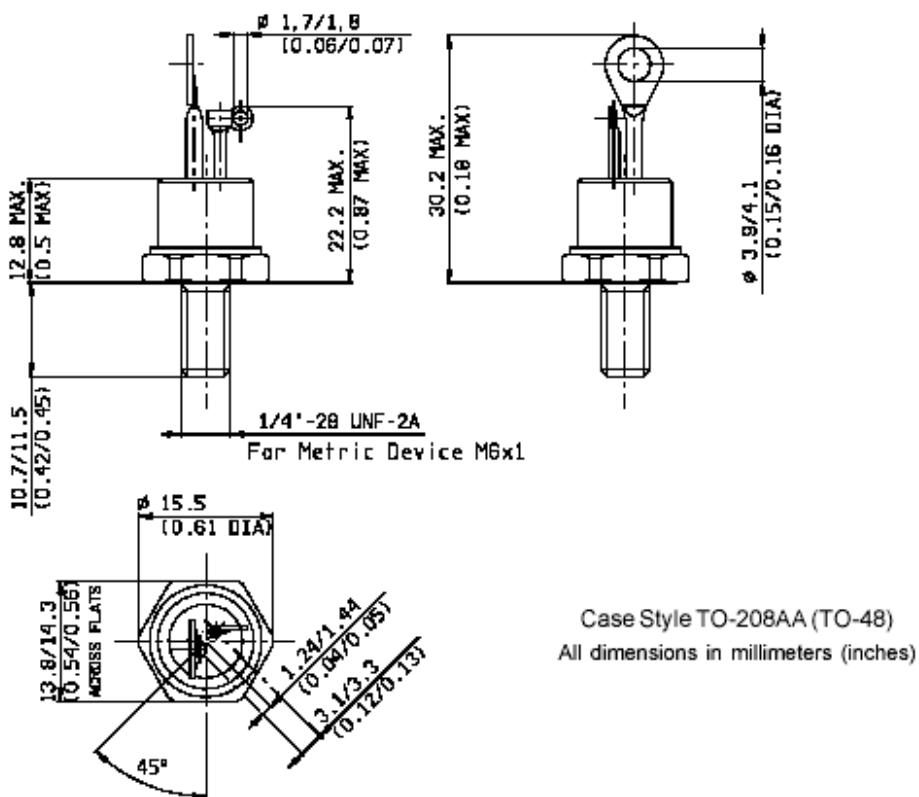
Parameter	10RIA120M	Units	Conditions
P _{GM} Maximum peak gate power	8.0	W	T _J = T _J max
P _{G(AV)} Maximum average gate power	2.0		
I _{GM} Max. peak positive gate current	1.5	A	T _J = T _J max
-V _{GM} Maximum peak negative gate voltage	10	V	T _J = T _J max
I _{GT} DC gate current required to trigger	90 60 35	mA	T _J = -40°C T _J = 25°C T _J = 125°C Max. required gate trigger current/voltage are the lowest value which will trigger all units 6V
V _{GT} DC gate voltage required to trigger	3.0 2.0 1.0	V	T _J = -40°C T _J = 25°C T _J = 125°C anode-to-cathode applied
I _{GD} DC gate current not to trigger	2.0	mA	T _J = T _J max. V _{DRM} =rated value
V _{GD} DC gate voltage not to trigger	0.25	V	T _J = T _J max. V _{DRM} =rated value Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V anode-to-cathode applied

Thermal and Mechanical Specification

Parameter	10RIA120M	Units	Conditions
T _J Max. operating temperature range	-40 to 125	°C	
T _{stg} Max. storage temperature range	-40 to 125		
R _{thJC} Max. thermal resistance, junction to case	0.86	K/W	DC operation
R _{thCS} Max. thermal resistance, case to heatsink	0.35		Mounting surface, smooth, flat and greased
T Mounting torque, ± 10%	2.8	Nm	
wt Approximate weight	12	g	

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Outline Table



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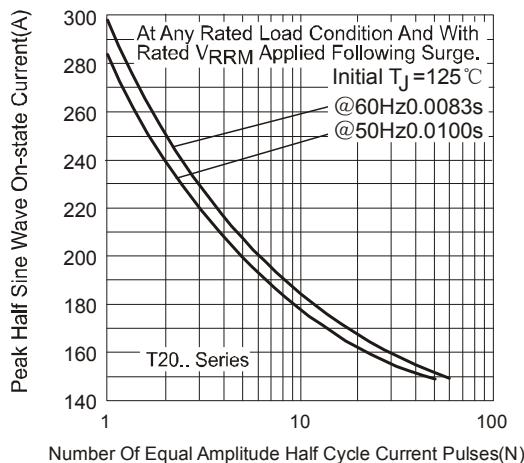


Fig.5-Maximum Non-Repetitive Surge Current

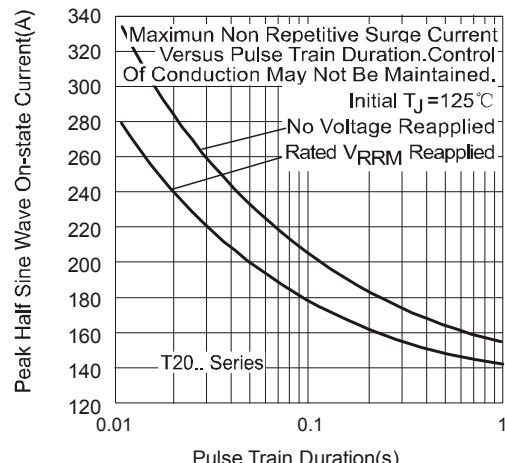


Fig.6-Maximum Non-Repetitive Surge Current

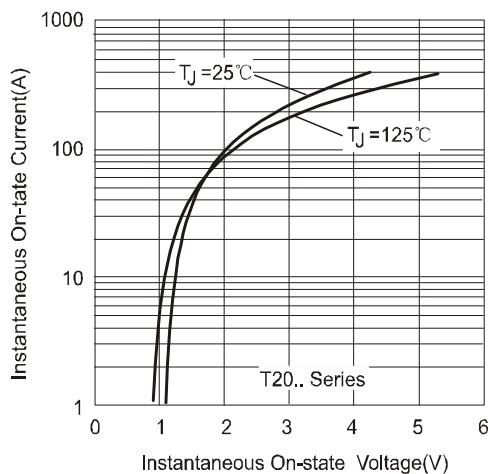
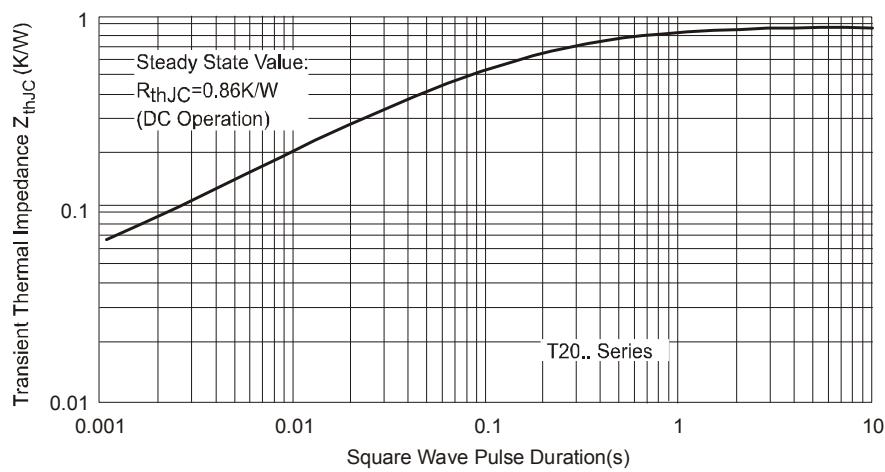


Fig.7-Forward Voltage Drop Characteristics

Fig.8-Thermal Impedance Z_{thJC} Characteristics

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